

Applied electronics

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Stato Completato

Terminato lunedì, 20 luglio 2020, 13:26

Tempo impiegato 6 min. 16 secondi

Valutazione Non ancora valutato

Domanda 1

Risposta corretta

Punteggio ottenuto

1,0 su 1,0

Consider a square wave generator realized with Schmitt trigger inverter; the voltage on the capacitor varies with time as:

- ☒ (a) exponential ✓
- ☐ (b) square wave
- ☐ (c) linear
- ☐ (d) is always zero

Risposta corretta.

La risposta corretta è: exponential

Domanda 2

Risposta corretta

Punteggio ottenuto

1,0 su 1,0

Consider a D-Latch active when LE is low ($\neq 0$). When $LE=0$:

- ☒ (a) the output state follows the input state D ✓
- ☐ (b) the output is always 1
- ☐ (c) the output is in memory state
- ☐ (d) the output is always 0

Risposta corretta.

La risposta corretta è: the output state follows the input state D

Domanda 3

Risposta corretta

Punteggio ottenuto

1,0 su 1,0

Consider a 4 bit weighted resistor DAC; the ratio between the resistance of the MSB branch (R_{MSB}) and the resistance of the LSB (R_{LSB}) branch is:

-
- ☒ (a) $R_{\text{MSB}}/R_{\text{LSB}}=0.125$ ✓
 - ☐ (b) $R_{\text{MSB}}/R_{\text{LSB}}=8$
 - ☐ (c) $R_{\text{MSB}}/R_{\text{LSB}}=0.5$
 - ☐ (d) $R_{\text{MSB}}/R_{\text{LSB}}=4$

Risposta corretta.

La risposta corretta è: $R_{\text{MSB}}/R_{\text{LSB}}=0.125$ **Domanda 4**

Risposta corretta

Punteggio ottenuto

1,0 su 1,0

The efficiency (ie: ratio between output and input power) of a series linear voltage regulator, with input V_i and output V_o can be approximated as:

-
- ☒ (a) V_o/V_i ✓
 - ☐ (b) V_i/V_o
 - ☐ (c) $V_o/(V_i+V_o)$
 - ☐ (d) $\sqrt{V_i/V_o}$

Risposta corretta.

La risposta corretta è: V_o/V_i **Domanda 5**

Risposta corretta

Punteggio ottenuto

1,0 su 1,0

If we double the clock frequency of a CMOS digital circuit, the dynamic power consumption will increase of a factor equal to:

-
- ☒ (a) 2 ✓
 - ☐ (b) 4
 - ☐ (c) 8
 - ☐ (d) does not change

Risposta corretta.

La risposta corretta è: 2

Domanda 6

Risposta corretta

Punteggio ottenuto

1,0 su 1,0

Consider a FPGA; a Look-Up Table (LUT) with 3 inputs needs:

- ☒ (a) 8 SRAM memory cells ✓
- ☐ (b) 8 FAMOS
- ☐ (c) 4 NAND gates and 8 NOR gates
- ☐ (d) 8 NAND gates and 4 NOR gates

Risposta corretta.

La risposta corretta è: 8 SRAM memory cells

Domanda 7

Risposta corretta

Punteggio ottenuto

1,0 su 1,0

The reflection coefficient of a matched termination of a transmission line is:

- ☒ (a) 0 ✓
- ☐ (b) 1
- ☐ (c) -1
- ☐ (d) 0.5

Risposta corretta.

La risposta corretta è: 0

Domanda 8

Risposta corretta

Punteggio ottenuto

1,0 su 1,0

V_o is the output voltage of a logic gate , choose the right condition for connecting V_o to the input of another logic gate (the voltage supply is V_{DD}):

- ☒ (a) $V_o = V_{ih} + NM$ ✓
- ☐ (b) $V_{il} < V_o < V_{ih}$
- ☐ (c) $V_o = V_{il} + NM$
- ☐ (d) $V_o < 0$
- ☐ (e) $V_o > V_{DD}$

Risposta corretta.

La risposta corretta è: $V_o = V_{ih} + NM$

Domanda 9

Risposta corretta

Punteggio ottenuto

1,0 su 1,0

Consider a NAND flash memory; the elementary units for erasing and writing operations are:

- ☒ (a) block (= erasing of several pages) and page (=elementary unit that can be written) ✓
- ☐ (b) page (=erasing of several blocks) and byte (=elementary unit that can be written)
- ☐ (c) block (= erasing of several pages) and byte (=elementary unit that can be written)

Risposta corretta.

La risposta corretta è: block (= erasing of several pages) and page (=elementary unit that can be written)

Domanda 10

Risposta corretta

Punteggio ottenuto

1,0 su 1,0

A DRAM memory cell consists in:

- ☒ (a) one MOS and one capacitor ✓
- ☐ (b) one FAMOS
- ☐ (c) 6 MOS
- ☐ (d) one MOS and 2 capacitors

Risposta corretta.

La risposta corretta è: one MOS and one capacitor

Domanda 11

Completo

Punteggio max.:

5,0

We have 4 analog input channels with voltage in the range between -0.5V and +0.5V. The maximum frequencies of the channels are $F_{\max,1} = 3 \text{ kHz}$, $F_{\max,2} = 2,5 \text{ kHz}$, $F_{\max,3} = 1 \text{ kHz}$, $F_{\max,4} = 2 \text{ kHz}$. The acquisition system uses only one S/H and only one tracking ADC with input dynamic range [0, +10 V]. The channels are oversampled with oversampling factor of 2.5.

Request 1:

List the various blocks of the acquisition system and define the role of each block. Indicate the relation V_{out} versus V_{in} of the conditioning amplifier .

Request 2:

Calculate the sampling frequency of the S/H

Request 3:

The ADC operates in overload condition; if the maximum ADC conversion time must be $T_c = 8.5 \mu\text{s}$, calculate the number of bits assuming that the clock frequency 250 MHz.

Request 4:

With the number of bits of previous point, calculate the SNRq for input sinusoidal signals

Request 1:

Conditioning amplifier: $A_v = 10$, offset +5V. $\Rightarrow V_o = A_v \cdot V_i + \text{offset}$

Request 2:

Sampling frequency of S/H is: $f_s = \max\{F_{\max,i}\} \cdot 2 \cdot 2.5 \cdot 4 = 3 \text{ kHz} \cdot 2 \cdot 2.5 \cdot 4 = 60 \text{ kHz} \Rightarrow T_s = 16.7 \mu\text{s}$

Request 3:

In overload condition, the conversion time is $T_c = 2^N \cdot T_{ck} = 8.5 \mu\text{s} \Rightarrow N = \log(8.5 \cdot 250) / \log(2) = 11$

Request 4:

$\text{SNRq} = (6 \cdot N + 1.76) \text{ dB} = 67.76 \text{ dB}$

Domanda 12

Completo

Punteggio max.: 5,0

One driver with $V_{dd}=3,3\text{ V}$ is connected on one side of a transmission line with $Z_{\infty} = 60\ \Omega$, propagation speed $U = 0,7\text{ C}$, length 15 cm and open circuit termination. The receivers are CMOS circuits with $V_{il} = 1\text{ V}$, $V_{ih} = 2,2\text{ V}$. Answer the following questions for a L->H transition:

Request 1:

Calculate the range of values of the output resistance of the driver (R_o) to drive the line in Reflective Wave Switching (RWS) mode and not in Incident Wave Switching mode, when only one receiver is connected at the near-end of the line.

Request 2:

With $R_o = 80\ \Omega$, calculate the maximum and minimum transmission times and the skew for a receiver connected in the near-end and a receiver connected in the far-end.

Request 3:

This interconnection is used for a parallel synchronous write bus protocol. The receiver registers have set-up time $T_{su} = 5\text{ ns}$ and hold time $T_h = 2\text{ ns}$. Calculate the delay between the DATA and STB signals and the duration of the write cycle.

Request 1:

In RWS mode the voltage at $V_b(2t_p)$ is the sum of the incident plus reflected voltage and must be recognized as high $\Rightarrow V_b(2t_p) = 2 \cdot Z_{\infty} / (Z_{\infty} + R_o) \cdot V_{dd} > V_{ih} \Rightarrow R_o < 120\ \Omega$

To avoid the switching on the first incident voltage step (IWS mode) we must set: $V_b(0) < V_{ih} \Rightarrow V_b(0) = Z_{\infty} / (Z_{\infty} + R_o) \cdot V_{dd} < V_{ih} \Rightarrow R_o > 30\ \Omega$

This implies:

$$30\ \Omega < R_o < 120\ \Omega$$

Request 2:

$$T_p = 0.71\text{ ns}$$

First incident voltage step: $V_b(0) = 1.4\text{ V} > V_{il} \Rightarrow$

For the receiver connected to the near-end:

$T_{txmin} = 0\text{ ns}$ because $V_b(0) > V_{il}$

$T_{txmax} = 2t_p$ because we need the back reflected voltage such that $> V_{ih}$

For the receiver connected to the far-end: $V_c(T_p) > V_{ih}$ always therefore

$$T_{txmin} = T_{txmax} = t_p$$

$$T_k = T_{txmax} - T_{txmin} = 2t_p = 1.42\text{ ns}$$

Request 3:

Delay between DATA and STB for the case of write cycle: $t_a = t_k + t_{su} = 1.42\text{ ns} + 5\text{ ns} = 6.42\text{ ns}$

Duration of the write cycle: $2t_k + t_{su} + t_h = 2 \cdot 1.42 + 5 + 2 = 9.84 \text{ ns}$

Domanda 13

Completo

Punteggio max.: 5,0

Consider the sequential circuit shown in the figure. All outputs Q are initially reset to zero. The block *f* is a combinational logic block with function $F = \text{not}(Q1 \cdot \text{not}(Q2))$. Assume $C=0$;

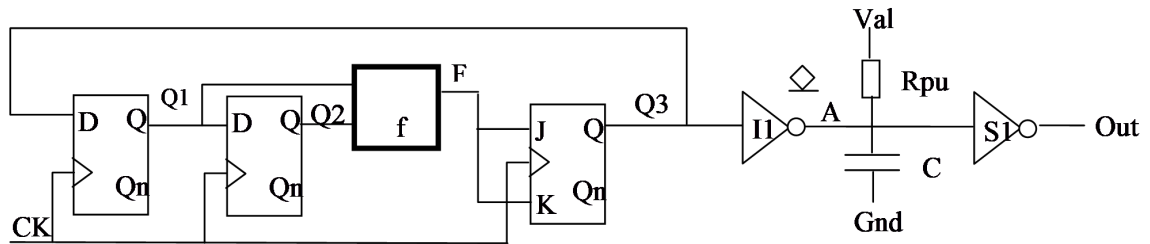
Dynamics parameters are:

FF D: $T_{ck \rightarrow Q} = 5 \text{ ns}$, $T_{su} = 4 \text{ ns}$;

FF JK: $T_{ck \rightarrow Q} = 7 \text{ ns}$, $T_{su} = 6 \text{ ns}$;

combinational logic block f: $TLH_f = 3 \text{ ns}$, $THL_f = 6 \text{ ns}$;

inverters I1 and S1: $TLH = 4 \text{ ns}$; $THL = 2 \text{ ns}$

**Request 1:**

Answer the following questions assuming the CK period is 60ns:

- which are the initial states of F, A and Out?
- how many CK rising edges are necessary to switch Q3 to high state?
- calculate the delay between a transition L->H of Q3 and the switch of Q1 to High
- calculate the delay between a transition L->H of Q3 and the switch of F to Low
- calculate the delay between a switch L->H of Q3 and the switch of the state OUT

Request 2:

Calculate the maximum CK frequency

Request 1:

Answer the following questions:

- which are the initial states of F, A and Out? **F=1; A=1; Out=0**
- how many CK rising edges are necessary to switch Q3 to high state? **F=1; J=K=1 therefore the JKFF swithes at the first CK rising edge**
- calculate the delay between a transition L->H of Q3 and the switch of Q1 : Q1 switches on the second rising edge of the CK, the delay between the L to H transition of Q3 and Q1 is : **(60-7)ns + 5 ns=58ns**
- calculate the delay between a transition L->H of Q3 and the switch of F: **F swithes to L as consequence of the transition to H of Q1. It is delayed respect to Q1 of 6ns. The delay respect to the transition of Q3 is 58+6ns=64ns.**
- calculate the delay between a switch L->H of Q3 and the switch of the state OUT: **we sum the delay for H->L transition of I1 (THL=2ns) and the delay for L->H transition of S1 (TLH=4ns). The total delay is (2+4)ns=6ns**

Request 2:

Calculate the maximum CK frequency

The worst case is for the FF JK :

$T_{ck} \rightarrow Q1,2 + T_{dmax} \text{ of } f + T_{suJK} = 5ns + 6ns + 6ns = 17ns$ $f_{ckmax} = 58.8MHz$

Domanda 14

Completo

Punteggio max.:

5,0

Consider a DRAM memory with 8 bit address (all 8 bits are used for row decoder) and 8 bit word. Pass transistors have drain parasitic capacitance $C_d = 0,2fF$ and threshold voltage $V_{th} = 0,1V$; voltage supply is $V_{dd} = 1V$. Answer to the following questions:

Request 1:

Calculate

- the number of bit lines
- the number of pass transistors connected to one bit line
- the total number of pass transistors of the memory.

Request 2:

Calculate the minimum value of the storage capacitor C_s , if the sense amplifier can sense a minimum voltage level of 70mV.

Request 1:

number of bitline: 8

number of rows: $2^8 = 256 \Rightarrow$ 256 pass transistor connected to one bit line

total number of pass transistor $256 * 8 = 2048$

Request 2:

The parasitic capacitance of the BL is: $C_{BL} = 2^8 * 0.2fF = 51.2fF$

The bitline variation of the voltage during the read must be sensed by the amplifier therefore must be higher than 70mV \Rightarrow

$$\Delta V_{bl} = C_s / (C_s + C_{bl}) * (V_{dd}/2 - V_{th}) > 70mV \Rightarrow C_s \geq 10.86fF$$

Domanda 15

Completo

Punteggio max.:

1,0

OPTIONAL Question on virtual lab:**Analog-to-digital and Digital-to-Analog converters**

Which components do you need in the LTspice software to realise and simulate a DAC circuit analogous to the one considered during the virtual LAB?

Domanda 16

Completo

Punteggio max.:

1,0

OPTIONAL Question on Virtual Lab**Logic gates and simple sequential logic circuits:**

How could you check using the LTspice software the correct operation of a synchronous counter such as the 4-bit CD4029 used during the virtual LAB?

Domanda 17

Completo

Punteggio max.:

1,0

OPTIONAL QUESTION on Virtual LAB**Transmission lines:**

How could you simulate and characterise with the LTspice software the effect of a capacitive load connected at the far end of a transmission line with matched termination? What do you expect to observe at the near end? Consider L to H transition.
